

/ Descriptions

Silicon NPN transistor in a TO-126F Plastic Package.

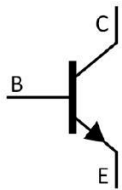
/ Features

High V_{CEO} .

/ Applications

High voltage amplifier, TV video output.

/ Equivalent Circuit



/ Pinning



PIN1 Emitter PIN 2 Collector PIN 3 Base

/ h_{FE} Classifications & Marking

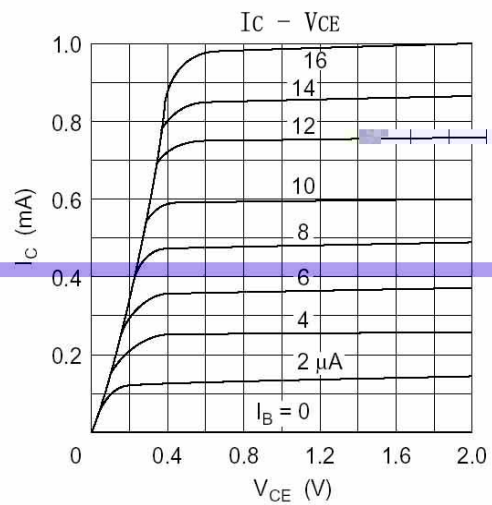
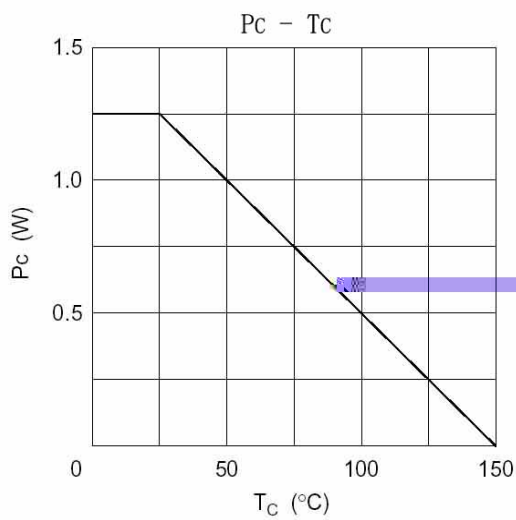
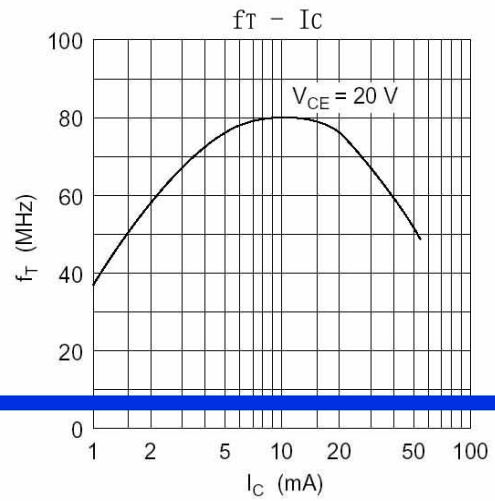
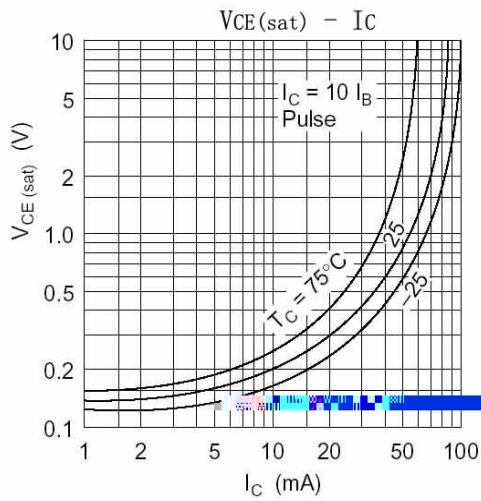
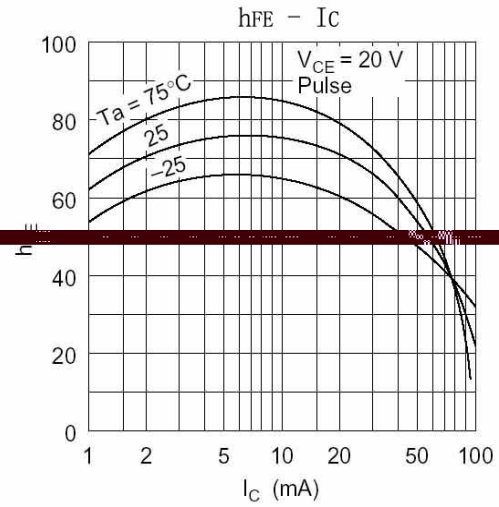
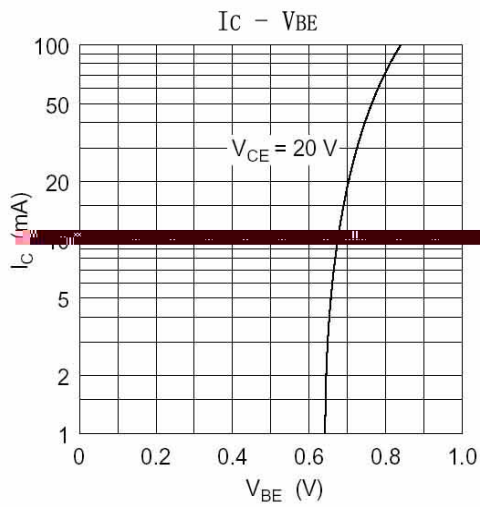
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	300	V
Collector to Emitter Voltage	V_{CEO}	300	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	100	mA
Collector Power Dissipation	P_C	1.25	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

CBO

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=10\mu A$ $I_E=0$	300			V
Collector to Emitter Breakdown Voltage	V_{CEO}					V

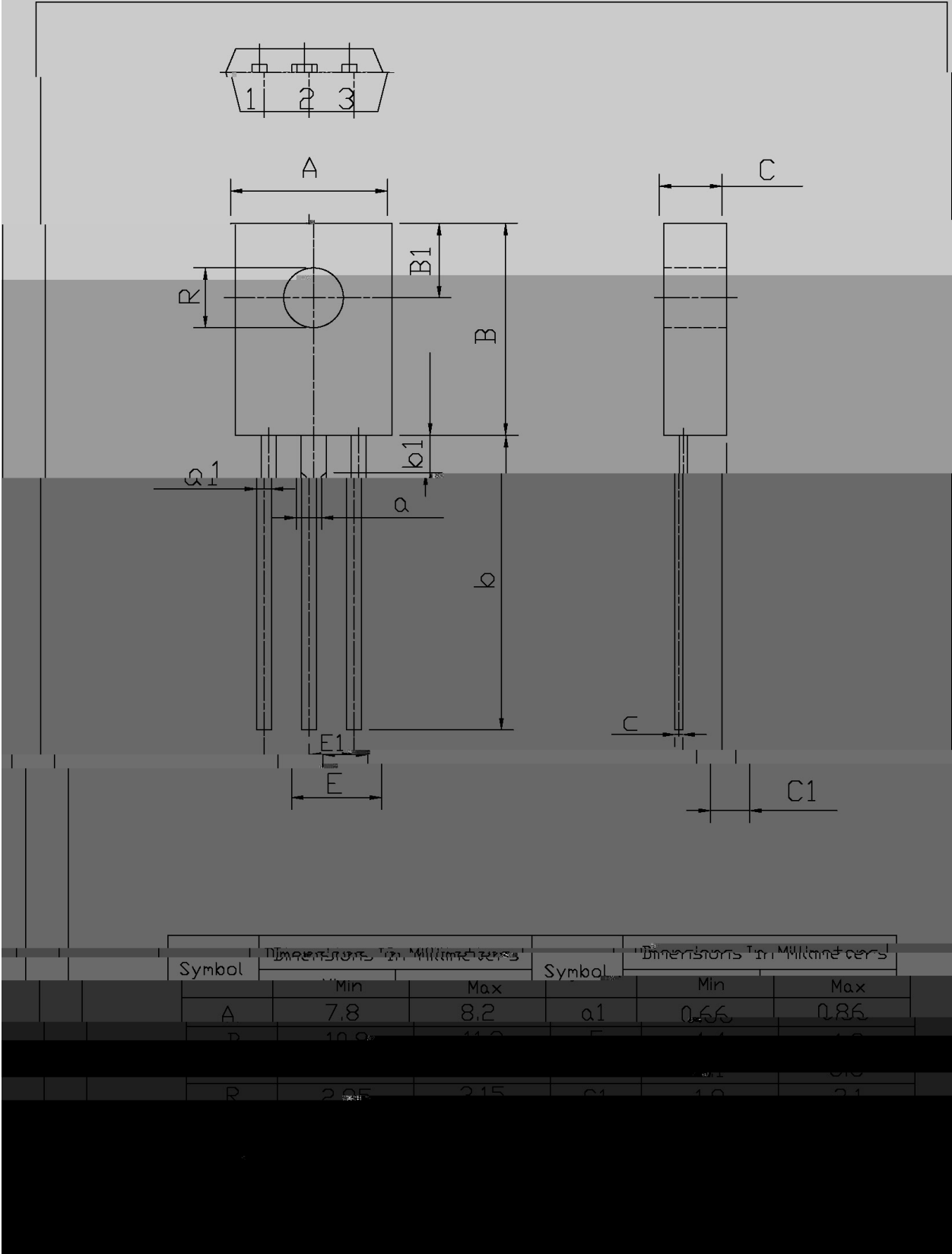
/ Electrical Characteristic Curve



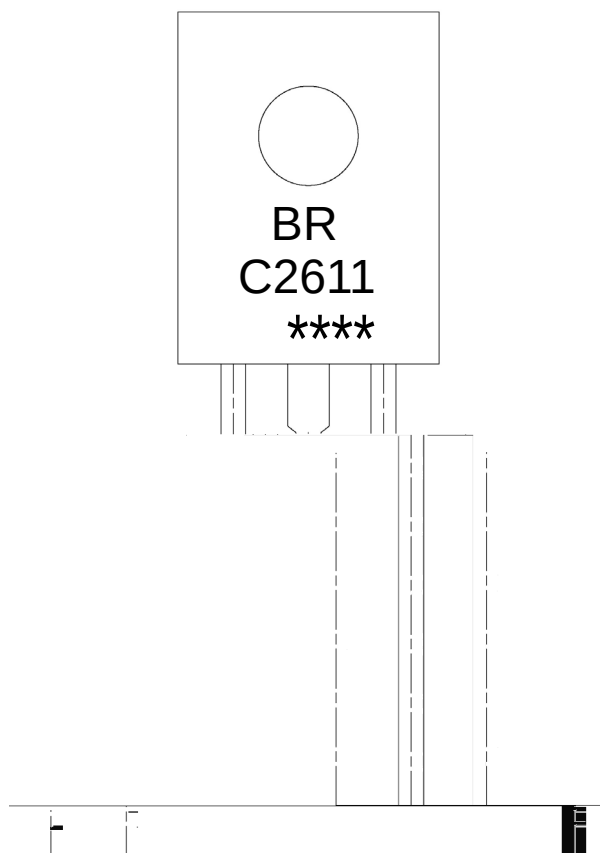
/ Package Dimensions

TU-126F

单位: mm



/ Marking Instructions



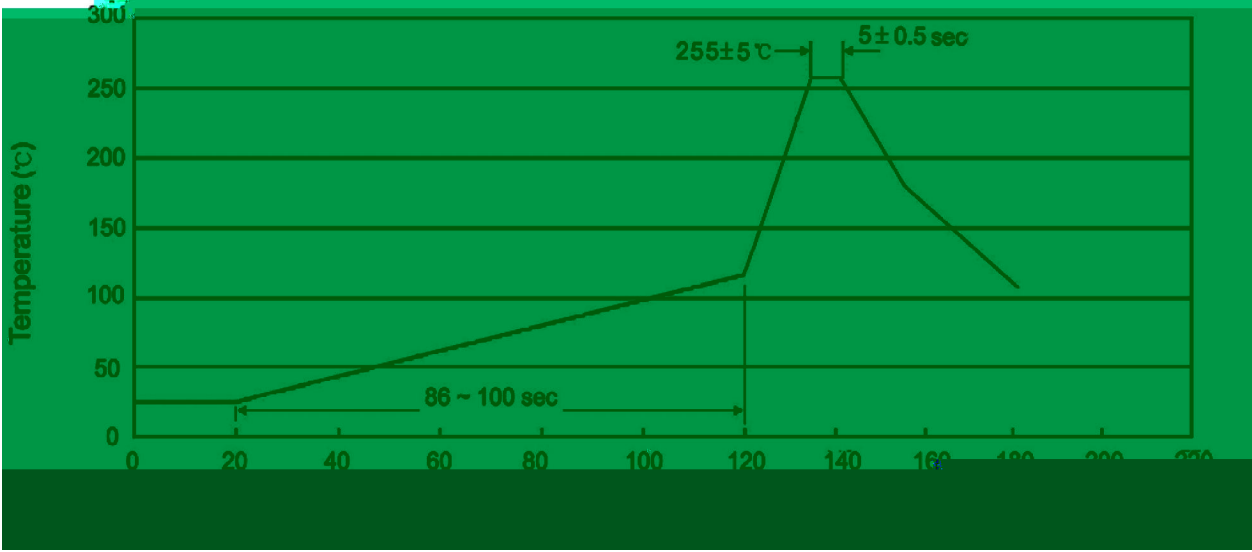
Note:

BR: Company Code

C2611: Product Type.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- 1

25 150

60 90sec;
- 2

255 5

5 0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:255 5

, Duration:5 0.5sec.
3. Cooling Speed: 2~10

/sec.

/ Resistance to Soldering Heat Test Conditions

270 5

10 1 sec.

Temp.:270±5℃

Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-126/F	500	6	3,000	5	15,000	135×190	237×172×102	560×245×195

/ TUBE

Package Type 封装形式	Units 包装数量	Dimension 包装尺寸 (unit: mm ³)
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